

66158

**SINGLE CHANNEL OPTOCOUPLER
DIRECT REPLACEMENT FOR 3C92C**



**OPTOELECTRONIC PRODUCTS
DIVISION**

Features:

- High Reliability
- Base lead eliminated for improved noise immunity
- Rugged package
- Stability over wide temperature
- +500V electrical isolation

Applications:

- Eliminate ground loops
- Level shifting
- Line receiver
- Switching power supplies
- Motor control

DESCRIPTION

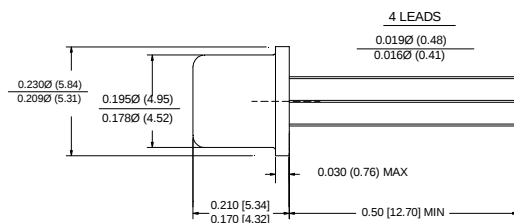
The **66158** contains a gallium arsenide infrared LED optically coupled to a silicon planar phototransistor. The optocoupler is built on a TO-46 header. The collector of the phototransistor is electrically connected to the case. This optocoupler is capable of transmitting signals between two galvanic sources. The potential difference between transmitter and receiver should not go over the maximum isolation voltage. The internal base connection has been eliminated for improved noise immunity.

ABSOLUTE MAXIMUM RATINGS

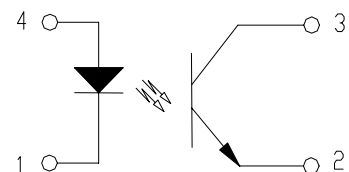
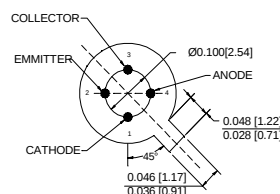
Input to Output Voltage	500V
Emitter-Collector Voltage	7V
Collector-Emitter Voltage (value applies to emitter-base open-circuited & the input-diode equal to zero)	60V
Reverse Input Voltage	7V
Input Diode Continuous Forward Current at (or below) 65°C Free-Air Temperature (see note 1)	50mA
Peak Forward Input Current (value applies for $t_w \leq 1\mu s$, PRR < 300 pps)	50mA
Continuous Collector Current.....	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 2).....	300mW
Storage Temperature	-65°C to +150°C
Operating Free-Air Temperature Range.....	-55°C to +100°C
Lead Solder Temperature (10 seconds max.)	240°C

Notes:

1. Derate linearly to 125°C free-air temperature at the rate of 0.67 mA/°C above 65°C.
2. Derate linearly to 125°C free-air temperature at the rate of 3 mW/°C.

Package Dimensions**Schematic Diagram**

DIMENSIONS ARE IN INCHES (MILLIMETERS)



ELECTRICAL CHARACTERISTICST_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode Static Reverse Current	I _R			1	μA	V _R = 3V
Input Diode Static Forward Voltage	V _F		1.15	1.2	V	I _F = 2mA
Input Diode Static Forward Voltage	V _F		1.3	1.5	V	I _F = 50mA
Reverse Breakdown Voltage	B _{VR}	7	12		V	I _R = 100μA
Input Diode Capacitance	C _{IN}		25		pF	V = 0V, f = 1MHz

OUTPUT TRANSISTORT_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50			V	I _C = 1mA, I _B = 0, I _F = 0
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	7			V	I _C = 10μA, I _E = 10μA, I _F = 0
Collector-Emitter Dark Current	I _{CEO1}			50	nA	V _{CE} = 50V, I _F = 0mA
	I _{CEO2}			10	nA	V _{CE} = 5V, I _F = 0mA

COUPLED CHARACTERISTICST_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
On State Collector Current	I _{C(ON)}	4			mA	V _{CE} = 5V, I _F = 10mA
On State Collector Current	I _{C(ON)}	3			mA	V _{CE} = 0.4V, I _F = 10mA
On State Collector Current -55°C	I _{C(ON)}	2			mA	V _{CE} = 5V, I _F = 10mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _F = 50mA, I _C = 10mA
Isolation Resistance	R _{ISO}	10 ⁹			Ω	V _{IN-OUT} = 500V
Input to Output Capacitance	C _{IO}		2	2.5	pF	f = 1MHz
Delay Time	t _d		2	4	μs	V _{CE} = 5V, I _F = 2mA, R _L = 100Ω
Storage Time	t _s		0.2	0.5	μs	V _{CE} = 5V, I _F = 2mA, R _L = 100Ω
Rise Time	t _r		3	5	μs	V _{CE} = 5V, I _F = 2mA, R _L = 100Ω
Fall Time	t _f		4	5	μs	V _{CE} = 5V, I _F = 2mA, R _L = 100Ω

RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	I _{FL}	0	1	μA
Input Current, High Level	I _{FH}	2	10	mA
Supply Voltage	V _{CE}	5	50	V
Operating Temperature	T _A	-55	125	°C

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION
66158-001	Single Channel optocoupler, military operating range (-55° to +125°C)
66158-101	Single Channel optocoupler, full mil-temp (-55° to +125°C) with 100% device screening
66158-011	Single Channel optocoupler, commercial (0° to 70°C)